HF / VHF power LDMOS transistor

AMPLEON

Rev. 1 — 26 March 2020

Product data sheet

1. Product profile

1.1 General description

A 500 W LDMOS power transistor for broadcast applications and industrial applications in the HF to 700 MHz band.

Table 1. Application information

Test signal	f	V _{DS}	PL	Gp	η _D
	(MHz)	(V)	(W)	(dB)	(%)
CW pulsed [1]	225	50	500	25.7	76
CW	225	50	500	25.3	77

^[1] $t_p = 100 \ \mu s; \ \delta = 10 \%.$

1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (10 MHz to 700 MHz)
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications

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2. Pinning information

Table 2. Pinning

Description	Simplified outline	Graphic symbol
drain1		
drain2	1 2	1
gate1	5	
gate2	3 4	3 - 5
source	[1]	4 —
		' <u></u>
		2 sym117
	drain1 drain2 gate1 gate2	drain1 drain2 gate1 gate2

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF974P	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	108	V
V_{GS}	gate-source voltage		-6	+11	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

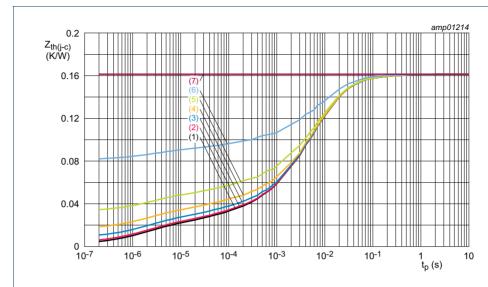
Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	$T_{case} = 90 ^{\circ}C; P_{L} = 500 W$ [1]	0.161	K/W
Z _{th(j-c)}	transient thermal impedance from junction to case	T_{case} = 90 °C; t_p = 100 μs; [2] $δ$ = 10 %	0.045	K/W

^[1] $R_{th(j-c)}$ is measured under RF conditions.

[2] See Figure 1.

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- (1) $\delta = 1 \%$
- (2) $\delta = 2 \%$
- (3) $\delta = 5 \%$
- (4) $\delta = 10 \%$
- (5) $\delta = 20 \%$
- (6) $\delta = 50 \%$
- (7) $\delta = 100 \% (DC)$

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

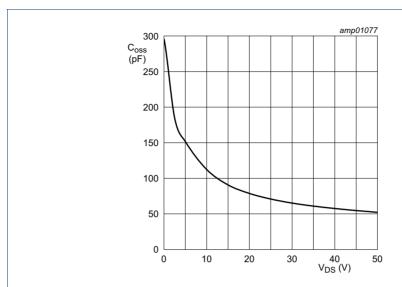
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.97 \text{ mA}$	108	-	-	V
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 197 \text{ mA}$	1.5	2.0	2.5	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 50 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	27.3	35.6	-	A
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 6.895 \text{ A}$	-	0.11	-	Ω

Table 7. AC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	0.74	-	pF
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	193	-	pF
C _{oss}	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	52.2	-	pF

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 $V_{GS} = 0 V$; f = 1 MHz.

Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

Table 8. RF characteristics

Test signal: CW pulsed; t_p = 100 μ s; δ = 10 %; f = 225 MHz; RF performance at V_{DS} = 50 V; I_{Dq} = 50 mA per section; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _L = 500 W	24.5	25.7	-	dB
RLin	input return loss	P _L = 500 W	-	-19	-15	dB
η_{D}	drain efficiency	P _L = 500 W	74	76	-	%

7. Test information

7.1 Ruggedness in class-AB operation

The BLF974P is capable of withstanding a load mismatch corresponding to VSWR = 13 : 1 through all phases under the following conditions: V_{DS} = 50 V; I_{Dq} = 50 mA per section; P_L = 500 W; f = 225 MHz; CW pulsed (t_p = 100 μ s; δ = 10 %).

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7.2 Impedance information

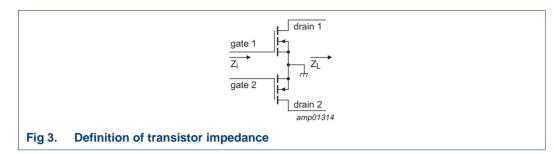


Table 9. Typical push-pull impedance

Simulated Z_i and Z_L device impedance; impedance info at $V_{DS} = 50 \text{ V}$ and $P_L = 500 \text{ W}$.

f	Z _i	Z_L
(MHz)	(Ω)	(Ω)
225	1.4 – j9.2	8.4 + j3.3

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7.3 Test circuit

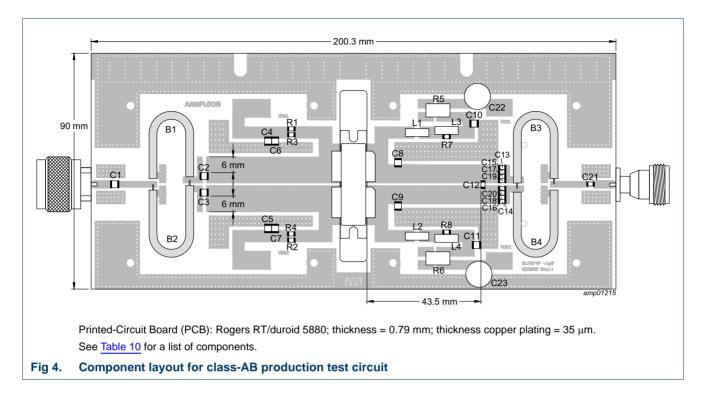


Table 10. List of components

For test circuit see Figure 4.

Component	Description	Value	Remarks
C1, C6, C7, C21	multilayer ceramic chip capacitor	1 nF	ATC 100B
C2, C3	multilayer ceramic chip capacitor	68 pF	ATC 100B
C4, C5, C10, C11	multilayer ceramic chip capacitor	4.7 μF, 100 V	C3225X7S2A475K200AE
C8, C9	multilayer ceramic chip capacitor	51 pF	ATC 100B
C12	multilayer ceramic chip capacitor	20 pF	ATC 800B
C13, C14, C15, C16, C17, C18	multilayer ceramic chip capacitor	10 pF	ATC 800B
C19, C20	multilayer ceramic chip capacitor	20 pF	ATC 800B
C22, C23	electrolytic capacitor	1500 μF, 80 V	
R1, R2	resistor	10 Ω	SMD 1206
R3, R4	resistor	4.7 Ω	SMD 1206
R5, R6	resistor	0.01 Ω	Ohmite: FC4L110R010FER
R7, R8	resistor	$2 \times 3.6 \Omega$, $0.6 W$	SMD 1206
L1, L2	1 mm copper wire	3 turns, D = 3 mm, I = 2.5 mm	
L3, L4	1 mm copper wire	4 turns, D = 3 mm, I = 3.5 mm	
B1, B2, B3, B4	coaxial line	50 Ω, 58 mm	HUBER+SUHNER: EZ-141-AL-TP-M17

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7.4 Graphical data

7.4.1 1-Tone CW pulsed

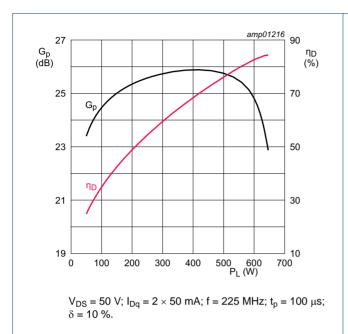
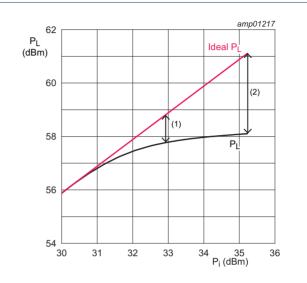


Fig 5. Power gain and drain efficiency as function of output power; typical values

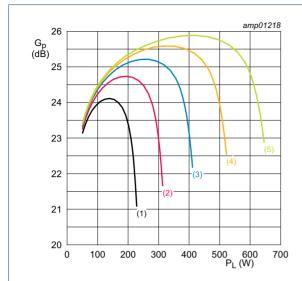


 V_{DS} = 50 V; I_{Dq} = 2 \times 50 mA; f = 225 MHz; t_p = 100 $\mu s;$ δ = 10 %.

- (1) $P_{L(1dB)} = 57.78 \text{ dBm } (600 \text{ W})$
- (2) $P_{L(3dB)} = 58.09 \text{ dBm } (645 \text{ W})$

Fig 6. Output power as a function of input power; typical values

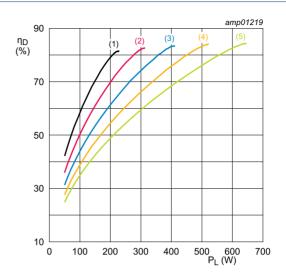
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 I_{Dq} = 2 \times 50 mA; f = 225 MHz; t_p = 100 $\mu s;$ δ = 10 %.

- (1) $V_{DS} = 30 \text{ V}$
- (2) $V_{DS} = 35 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 45 \text{ V}$
- (5) $V_{DS} = 50 \text{ V}$

Fig 7. Power gain as a function of output power; typical values

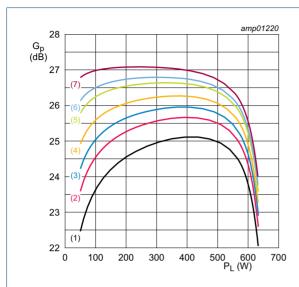


 I_{Dq} = 2 \times 50 mA; f = 225 MHz; t_p = 100 $\mu s;$ δ = 10 %.

- (1) $V_{DS} = 30 \text{ V}$
- (2) $V_{DS} = 35 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 45 \text{ V}$
- (5) $V_{DS} = 50 \text{ V}$

Fig 8. Drain efficiency as a function of output power; typical values

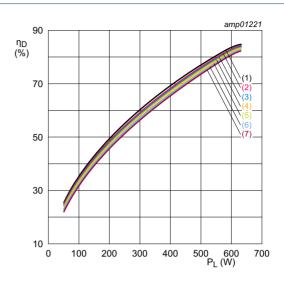
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 V_{DS} = 50 V; f = 225 MHz; t_p = 100 $\mu s;$ δ = 10 %.

- (1) $I_{Dq} = 2 \times 10 \text{ mA}$
- (2) $I_{Dq} = 2 \times 50 \text{ mA}$
- (3) $I_{Dq} = 2 \times 100 \text{ mA}$
- (4) $I_{Dq} = 2 \times 200 \text{ mA}$
- (5) $I_{Dq} = 2 \times 400 \text{ mA}$
- (6) $I_{Dq} = 2 \times 500 \text{ mA}$
- (7) $I_{Dq} = 2 \times 750 \text{ mA}$

Fig 9. Power gain as a function of output power; typical values



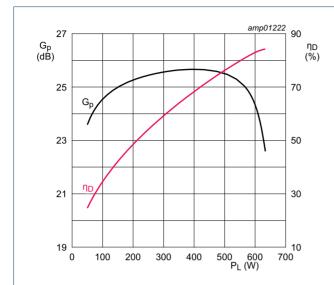
 V_{DS} = 50 V; f = 225 MHz; t_p = 100 $\mu s;$ δ = 10 %.

- (1) $I_{Dq} = 2 \times 10 \text{ mA}$
- (2) $I_{Dq} = 2 \times 50 \text{ mA}$
- (3) $I_{Dq} = 2 \times 100 \text{ mA}$
- (4) $I_{Dq} = 2 \times 200 \text{ mA}$
- (5) $I_{Dq} = 2 \times 400 \text{ mA}$
- (6) $I_{Dq} = 2 \times 500 \text{ mA}$
- (7) $I_{Dq} = 2 \times 750 \text{ mA}$

Fig 10. Drain efficiency as a function of output power; typical values

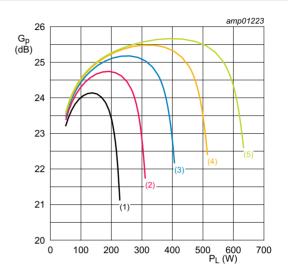
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7.4.2 1-Tone CW



 V_{DS} = 50 V; I_{Dq} = 2 × 50 mA; f = 225 MHz.

Fig 11. Power gain and drain efficiency as function of output power; typical values

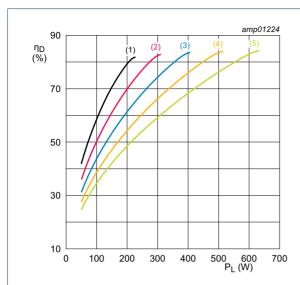


 $I_{Dq} = 2 \times 50 \text{ mA}$; f = 225 MHz.

- (1) $V_{DS} = 30 \text{ V}$
- (2) $V_{DS} = 35 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 45 \text{ V}$
- (5) $V_{DS} = 50 \text{ V}$

Fig 12. Power gain as a function of output power; typical values

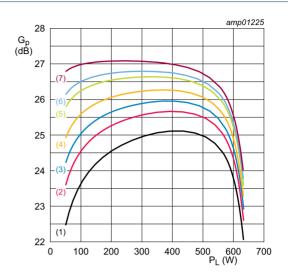
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$$I_{Dq} = 2 \times 50 \text{ mA}$$
; f = 225 MHz.

- (1) $V_{DS} = 30 \text{ V}$
- (2) $V_{DS} = 35 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 45 \text{ V}$
- (5) $V_{DS} = 50 \text{ V}$

Fig 13. Drain efficiency as a function of output power; typical values

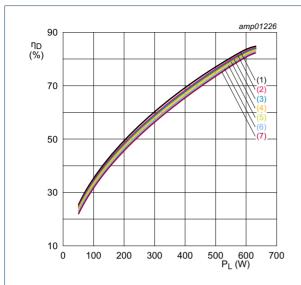


 $V_{DS} = 50 \text{ V}$; f = 225 MHz.

- (1) $I_{Dq} = 2 \times 10 \text{ mA}$
- (2) $I_{Dq} = 2 \times 50 \text{ mA}$
- (3) $I_{Dq} = 2 \times 100 \text{ mA}$
- (4) $I_{Dq} = 2 \times 200 \text{ mA}$
- (5) $I_{Dq} = 2 \times 400 \text{ mA}$
- (6) $I_{Dq} = 2 \times 500 \text{ mA}$
- (7) $I_{Dq} = 2 \times 750 \text{ mA}$

Fig 14. Power gain as a function of output power; typical values

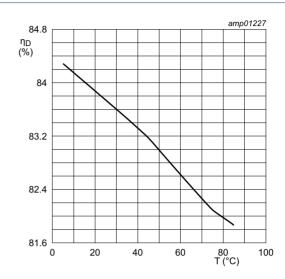
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 $V_{DS} = 50 \text{ V}$; f = 225 MHz.

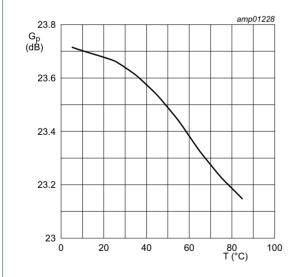
- (1) $I_{Dq} = 2 \times 10 \text{ mA}$
- (2) $I_{Dq} = 2 \times 50 \text{ mA}$
- (3) $I_{Dq} = 2 \times 100 \text{ mA}$
- (4) $I_{Dq} = 2 \times 200 \text{ mA}$
- (5) $I_{Dq} = 2 \times 400 \text{ mA}$
- (6) $I_{Dq} = 2 \times 500 \text{ mA}$
- (7) $I_{Dq} = 2 \times 750 \text{ mA}$

Fig 15. Drain efficiency as a function of output power; typical values



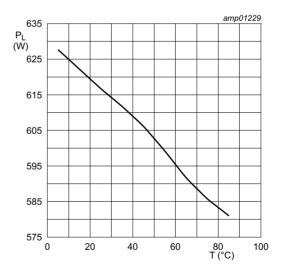
 $V_{DS} = 50 \text{ V}$; $I_{Dq} = 2 \times 50 \text{ mA}$; f = 225 MHz; at $P_{L(2dB)}$.





 V_{DS} = 50 V; I_{Dq} = 2 × 50 mA; f = 225 MHz; at $P_{L(2dB)}$.

Fig 17. Power gain as a function of temperature; typical values

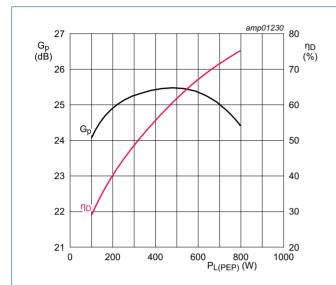


 V_{DS} = 50 V; I_{Dq} = 2 × 50 mA; f = 225 MHz; at $P_{L(2dB)}$.

Fig 18. Output power as a function of temperature; typical values

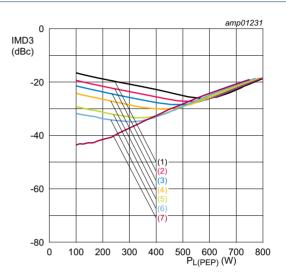
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7.4.3 2-Tone CW



 V_{DS} = 50 V; I_{Dq} = 2 × 50 mA; f_1 = 224.95 MHz; f_2 = 225.05 MHz.

Fig 19. Power gain and drain efficiency as functions of peak envelope load power; typical values



 $V_{DS} = 50 \text{ V}$; $f_1 = 224.95 \text{ MHz}$; $f_2 = 225.05 \text{ MHz}$.

- (1) $I_{Dq} = 2 \times 10 \text{ mA}$
- (2) $I_{Dq} = 2 \times 50 \text{ mA}$
- (3) $I_{Dq} = 2 \times 100 \text{ mA}$
- (4) $I_{Dq} = 2 \times 200 \text{ mA}$
- (5) $I_{Dq} = 2 \times 400 \text{ mA}$
- (6) $I_{Dq} = 2 \times 500 \text{ mA}$
- (7) $I_{Dq} = 2 \times 750 \text{ mA}$

Fig 20. Third order intermodulation distortion as a function of peak envelope load power; typical values

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8. Package outline

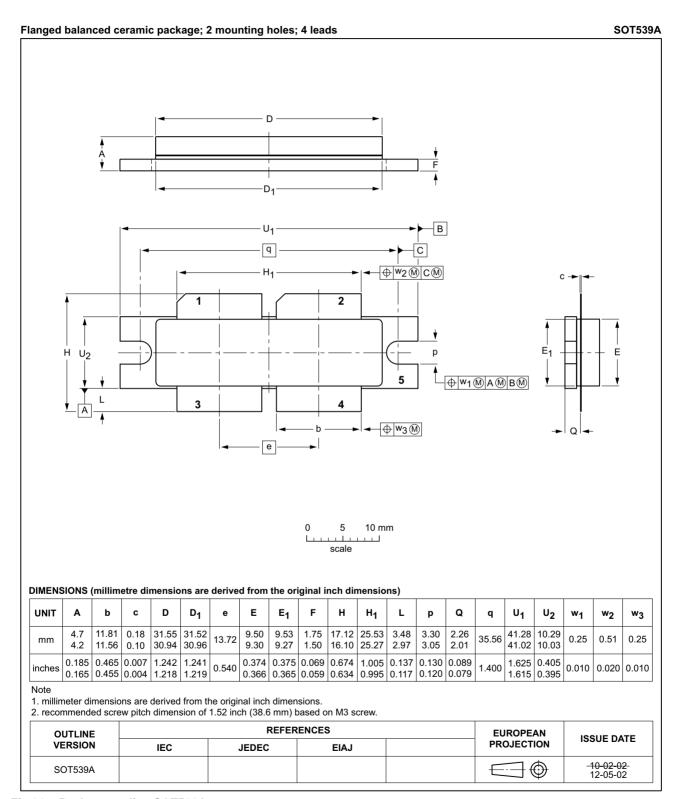


Fig 21. Package outline SOT539A

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9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

10. Abbreviations

Table 12. Abbreviations

Acronym	Description
CW	Continuous Wave
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
RoHS	Restriction of Hazardous Substances
SMD	Surface Mounted Device
VHF	Very High Frequency
VSWR	Voltage Standing Wave Ratio

11. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF974P v.1	20200326	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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13. Contact information

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For sales office addresses, please visit: http://www.ampleon.com/sales

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